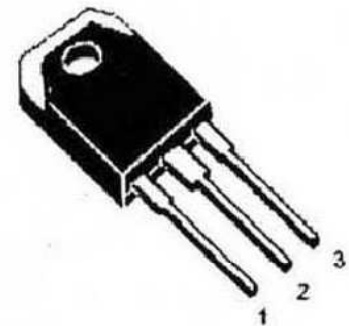


# T0-3PN Plastic-Encapsulate Transistors

## D4515 TRANSISTOR(NPN)

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Characteristic              | Symbol | Value    | Unit |
|-----------------------------|--------|----------|------|
| Collector-Base Voltage      | VCBO   | 700      | V    |
| Collector-Emitter Voltage   | VCEO   | 400      | V    |
| Emitter-Base voltage        | VEBO   | 9        | V    |
| Collector Current           | Ic     | 15       | A    |
| Collector Power Dissipation | Pc     | 120      | W    |
| Junction Temperature        | Tj     | 150      | °C   |
| Storage Temperature         | Tstg   | -55~+150 | °C   |



T0-3PN

ELECTRICAL CHARACTERISTICS (Ta=25°C , unless otherwise specified)

| Characteristic                         | Symbol   | Test conditions  | MIN | TYP | MAX | Unit |
|----------------------------------------|----------|------------------|-----|-----|-----|------|
| Collector -base breakdown voltage      | V(BR)CBO | Ic=1000μA ,IE=0  | 700 |     |     | V    |
| *Collector -emitter Sustaining Voltage | V(BR)CEO | Ic=10mA ,IB=0    | 400 |     |     | V    |
| Emitter cut-off current                | IEBO     | VEB=9V, IC=0     |     |     | 10  | μA   |
| DC current gain                        | hFE(1)   | VCE=5V, IC=2A    | 15  |     | 50  |      |
|                                        | hFE(2)   | VCE=5V, IC=5A    | 10  |     |     |      |
|                                        | hFE(3)   | VCE=5V, IC=10A   | 8   |     |     |      |
| Collector -emitter saturation voltage  | VCE(sat) | IC=10A, IB=2A    |     |     | 1   | V    |
| Base-emitter saturation voltage        | VBE(sat) | IC=10A, IB=2A    |     |     | 1.5 | V    |
| Base Emitter Voltage                   | VBE(ON)  | IE= 2000 mA      |     |     | 3   | V    |
| Current Gain Bandwidth Product         | fT       | VCE=10V, Ic=0.5A | 4   |     |     | MHZ  |
| Turn On Time                           | TON      |                  |     |     |     | μs   |
| Storage Time                           | ts       | VCC=24V IC=6A,   |     |     | 3   | μs   |
| Fall Time                              | tf       | IB1=- IB2=1.2A   |     |     | 0.7 | μs   |